

MOSFET - Power, Single N-Channel, STD Gate, μ 8FL 40 V, 1.43 m Ω , 178 A

NVTFWS1D3N04XM

Features

- Low RDS(on) to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Small Footprint (3.3 x 3.3 mm) for Compact Design
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Motor Drive
- Battery Protection
- Synchronous Rectification

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	40	V
Gate-to-Source Voltage	DC V _{GS}	±20	V
Continuous Drain Current	I _D	T _C = 25°C	178 A
		T _C = 100°C	126
Power Dissipation	T _A = 25°C	P _D	83 W
Pulsed Drain Current	T _C = 25°C, t _p = 10 μ s	I _{DM}	895 A
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C
Source Current (Body Diode)	I _S	71	A
Single Pulse Avalanche Energy (I _{LPK} = 17.2 A)	E _{AS}	281	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

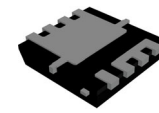
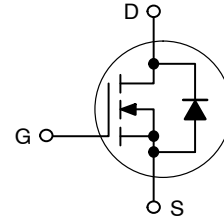
THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Note 2)	R _{θJC}	1.8	°C/W
Thermal Resistance, Junction-to-Ambient (Notes 1, 2)	R _{θJA}	46.4	

1. Surface mounted on FR4 board using 650 mm², 2 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

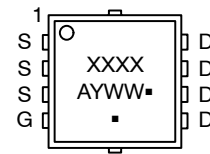
V _{(BR)DSS}	R _{DS(on)} TYP	I _D MAX
40 V	1.43 m Ω @ 10 V	178 A

N-CHANNEL MOSFET



WDFNW8
(μ 8FL)
CASE 515AP

MARKING DIAGRAM



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NVTFWS1D3N04XM

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	40	-	-	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	$I_D = 1\text{ mA}$, Referenced to 25°C	-	15	-	mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{ V}, T_J = 25^\circ\text{C}$	-	-	1	μA
		$V_{DS} = 40\text{ V}, T_J = 125^\circ\text{C}$	-	-	100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 25^\circ\text{C}$	-	1.24	1.43	m Ω
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 90\text{ }\mu\text{A}, T_J = 25^\circ\text{C}$	2.5	3	3.5	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(th)}/\Delta T_J$	$V_{GS} = V_{DS}, I_D = 90\text{ }\mu\text{A}$	-	-7.34	-	mV/ $^\circ\text{C}$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 20\text{ A}$	-	103	-	S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	2288	-	μF
Output Capacitance	C_{OSS}		-	1449	-	
Reverse Transfer Capacitance	C_{RSS}		-	22	-	
Total Gate Charge	$Q_{G(tot)}$	$V_{DD} = 32\text{ V}, I_D = 50\text{ A}, V_{GS} = 10\text{ V}$	-	36	-	nC
Threshold Gate Charge	$Q_{G(th)}$		-	7	-	
Gate-to-Source Charge	Q_{GS}		-	11	-	
Gate-to-Drain Charge	Q_{GD}		-	7	-	
Gate Resistance	R_G	$f = 1\text{ MHz}$	-	0.7	-	Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 0/10\text{ V}, I_D = 50\text{ A}, V_{DD} = 32\text{ V}, R_G = 0\text{ }\Omega$	-	21	-	ns
Rise Time	t_r		-	8	-	
Turn-Off Delay Time	$t_{d(off)}$		-	34	-	
Fall Time	t_f		-	8	-	

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$I_S = 20\text{ A}, V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	-	0.79	1.2	V
		$I_S = 20\text{ A}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$	-	0.64	-	
Reverse Recovery Time	t_{rr}	$V_{GS} = 0\text{ V}, I_S = 50\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_{DD} = 32\text{ V}$	-	48	-	ns
Charge Time	t_a		-	20	-	
Discharge Time	t_b		-	28	-	
Reverse Recovery Charge	Q_{RR}		-	48	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL PERFORMANCE CHARACTERISTICS

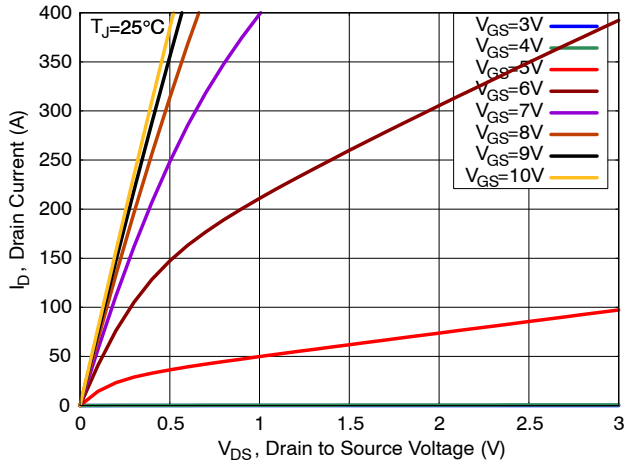


Figure 1. On-Region Characteristics

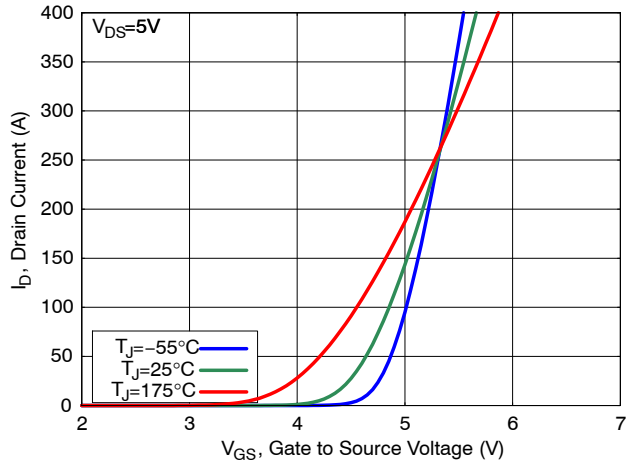


Figure 2. Transfer Characteristics

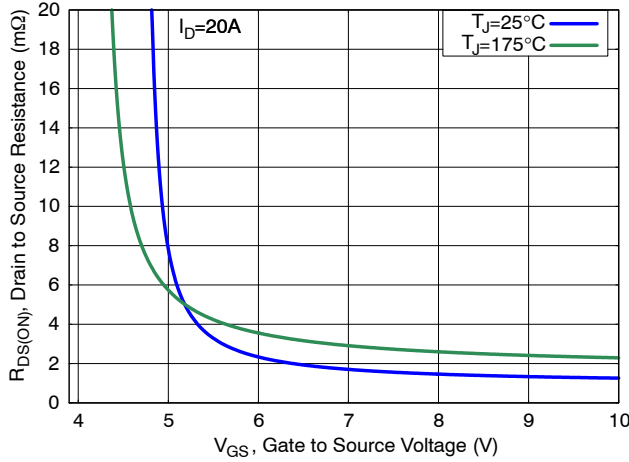


Figure 3. On-Resistance vs. Gate Voltage

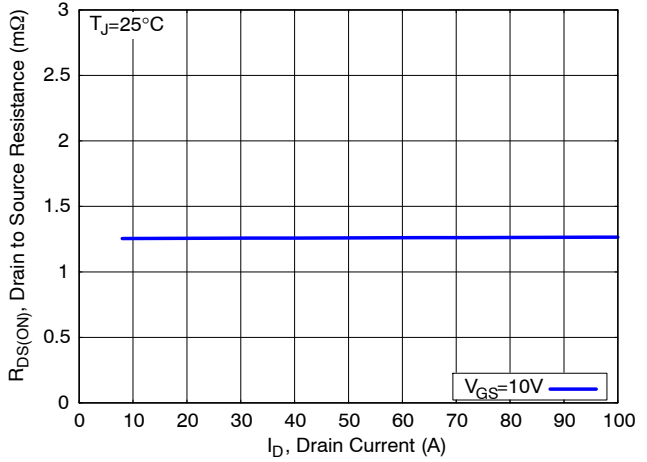


Figure 4. On-Resistance vs. Drain Current

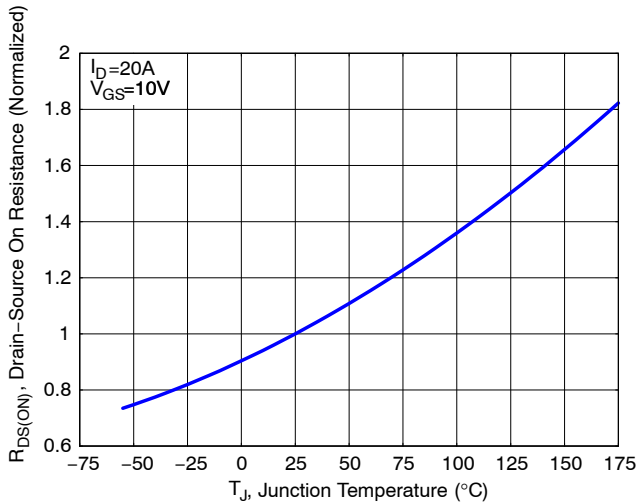


Figure 5. Normalized ON Resistance vs. Junction Temperature

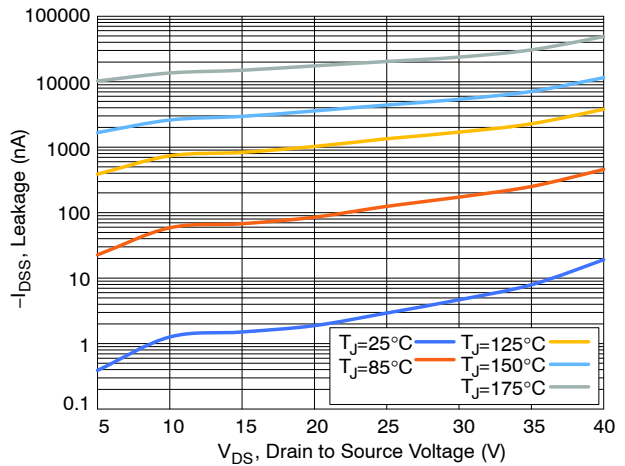


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL PERFORMANCE CHARACTERISTICS

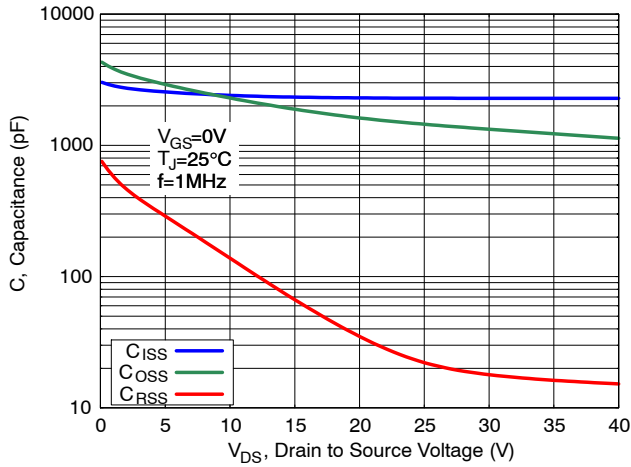


Figure 7. Capacitance Characteristics

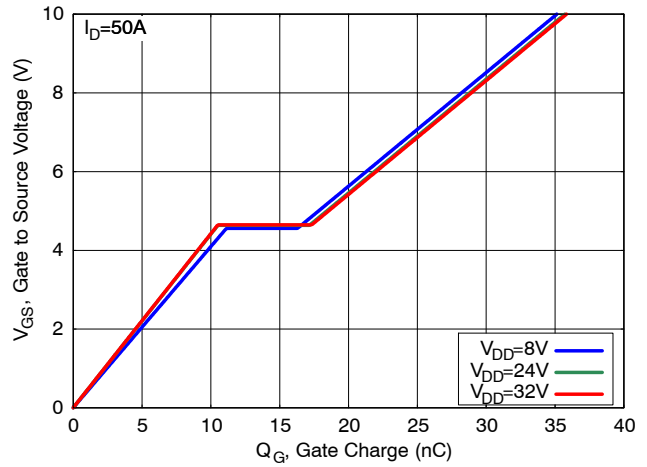


Figure 8. Gate Charge Characteristics

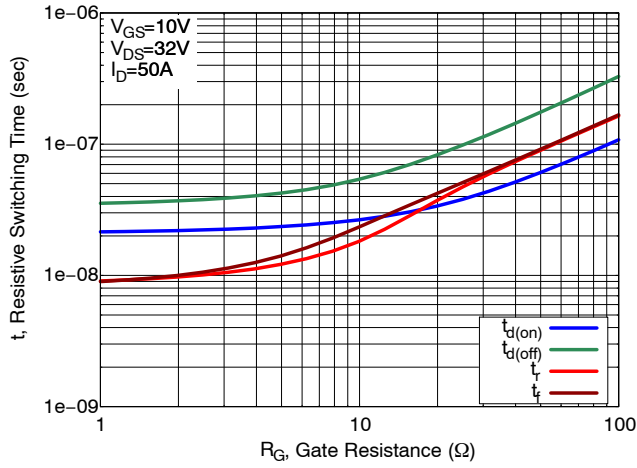


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

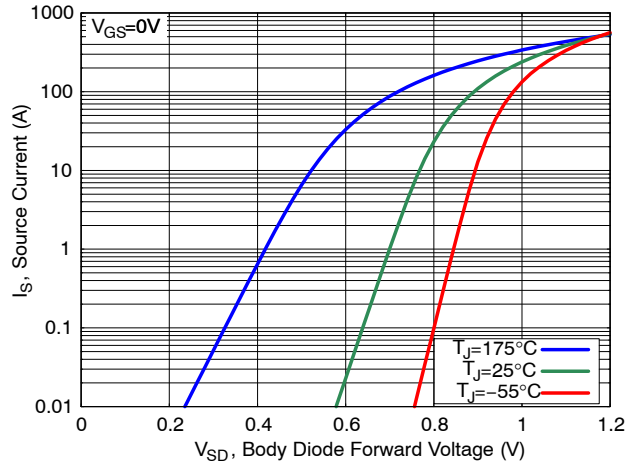


Figure 10. Diode Forward Characteristics

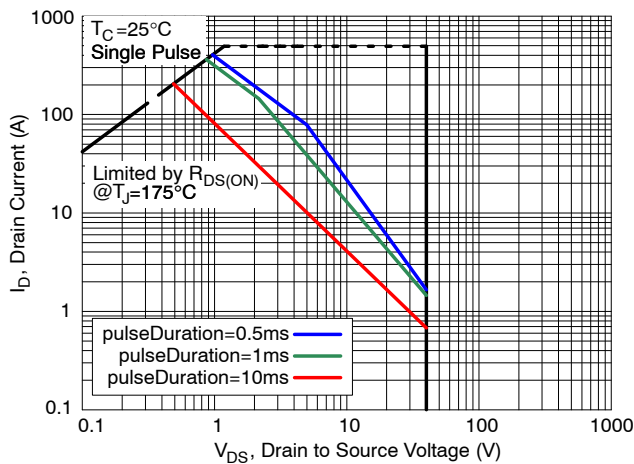


Figure 11. Safe Operating Area (SOA)

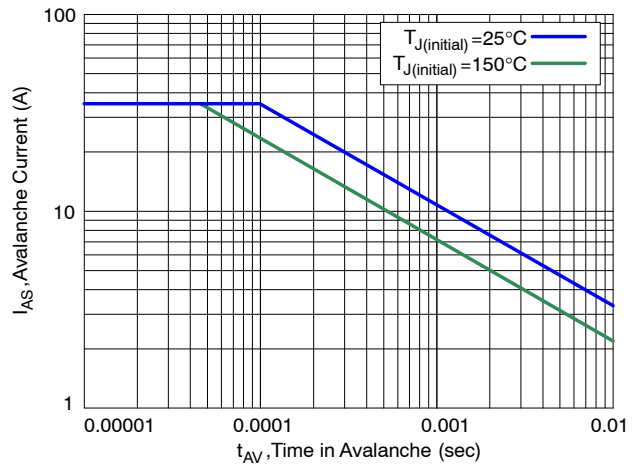


Figure 12. Avalanche Current vs. Pulse Time (UIS)

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TYPICAL PERFORMANCE CHARACTERISTICS

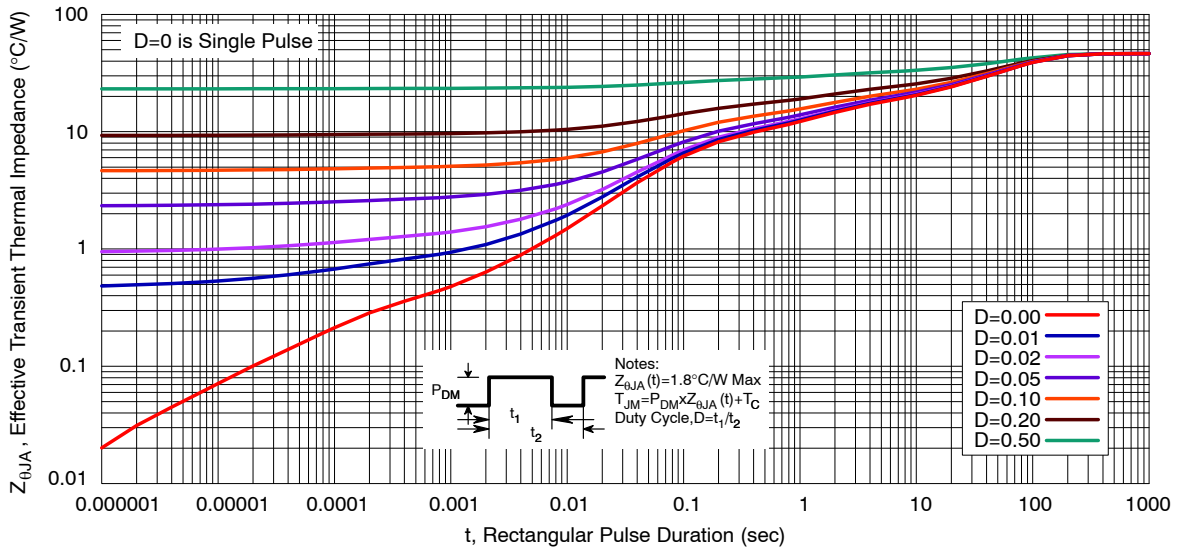
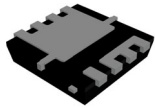


Figure 13. Transient Thermal Response

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NVTFWS1D3N04XMTAG	1D3W	WDFNW8	Tape & Reel	N/A	N/A	1500 Units

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

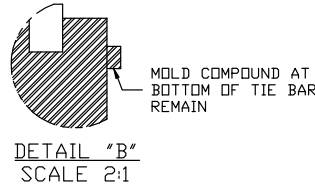
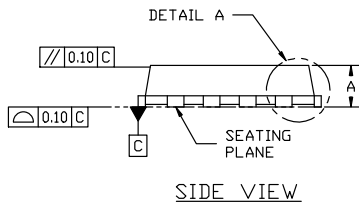
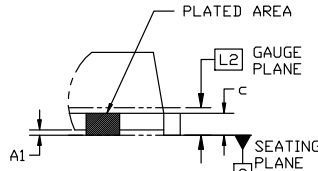
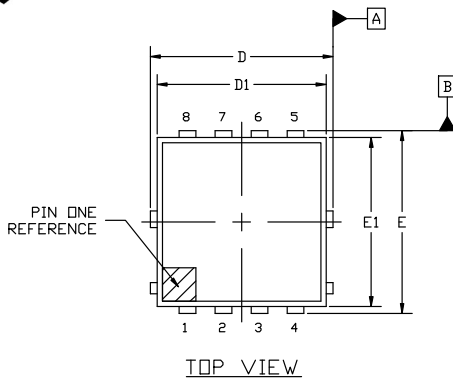


WDFNW8 3.30x3.30x0.75, 0.65P CASE 515AP ISSUE A

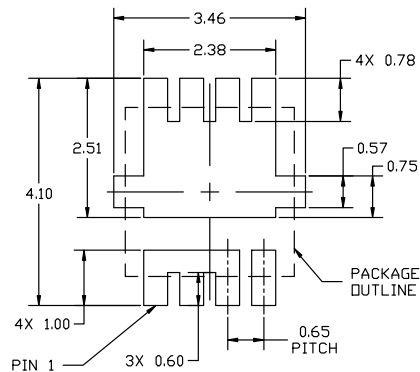
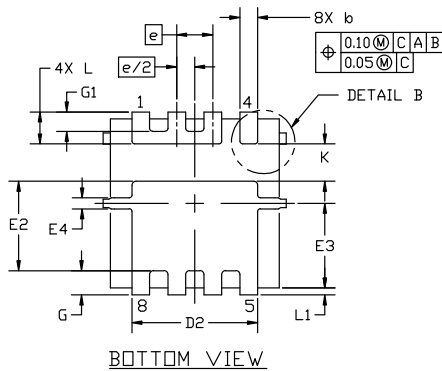
DATE 07 NOV 2023

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. FULL-CUT u8FL FUSED WF.



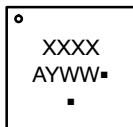
DIM	MILLIMETERS		
	MIN.	NDM.	MAX.
A	0.70	0.75	0.80
A1	0.00	----	0.05
b	0.23	0.33	0.43
c	0.15	0.20	0.25
D	3.20	3.30	3.40
D1	2.95	3.13	3.30
D2	1.98	2.20	2.40
E	3.20	3.30	3.40
E1	2.80	3.00	3.15
E2	1.40	1.60	1.80
E3	1.35	1.50	1.60
E4	0.15	0.25	0.40
e	0.65 BSC		
G	0.30	0.43	0.55
G1	0.25	0.35	0.45
K	0.55	0.75	0.95
L	0.35	0.52	0.65
L1	0.06	0.15	0.30
L2	0.25 BSC		



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

(Note: Microdot may be in either location)

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